

IN THE SPECIFICATION

Please amend the paragraph at column 11, lines 26-32 as follows:

The oxide film 16 is then etched, if necessary, after photolithography process, and the gate insulating film 7 and silicon oxide film 161 of silicon oxide [is] are formed by thermal oxidation. The gate electrode 8 of polysilicon is formed on the surface of the gate insulating film 7 after photolithography process (FIG. 8).